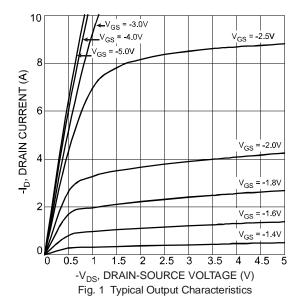


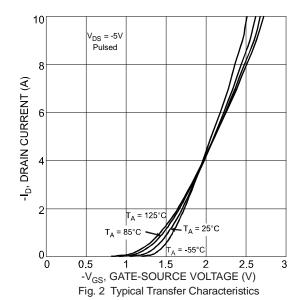
Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
STATIC PARAMETERS								
Drain-Source Breakdown Voltage	BV _{DSS}	-20	_	_	V	$I_D = -250 \mu A, V_{GS} = 0 V$		
Zero Gate Voltage Drain Current T _J = 25°C	I _{DSS}	_	_	-1	μА	V _{DS} = -20V, V _{GS} = 0V		
Gate-Body Leakage Current	I _{GSS}	_	_	±100	nA	$V_{DS} = 0V, V_{GS} = \pm 12V$		
Gate Threshold Voltage	$V_{GS(th)}$	-0.6	_	-1.25	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$		
On State Drain Current (Note 5)	I _{D (ON)}	-15	_		Α	$V_{GS} = -4.5V, V_{DS} = -5V$		
		_	51	80		$V_{GS} = -4.5V$, $I_D = -4.5A$		
Static Drain-Source On-Resistance (Note 5)	R _{DS (ON)}		82	110		$V_{GS} = -2.7V$, $I_D = -3.8A$		
			94	130		$V_{GS} = -2.5V, I_D = -3.7A$		
Forward Transconductance (Note 5)	g _{FS}	_	6.3	_	S	$V_{DS} = -10V, I_D = -4.5A$		
Diode Forward Voltage (Note 5)	V_{SD}	_	0.79	-1.26	V	$I_S = -1.7A$, $V_{GS} = 0V$		
Maximum Body-Diode Continuous Current (Note 1)		_		1.7	Α	_		
DYNAMIC PARAMETERS (Note 6)								
Total Gate Charge		_	7.3		nC	$V_{GS} = -4.5V$, $V_{DS} = -10V$, $I_{D} = 4.5A$		
Gate-Source Charge		_	2.0	_	nC	$V_{GS} = -4.5V$, $V_{DS} = -10V$, $I_D = 4.5A$		
Gate-Drain Charge		_	1.9	_	nC	$V_{GS} = -4.5V$, $V_{DS} = -10V$, $I_D = 4.5A$		
Turn-On Delay Time	t _{D(on)}	_	12	_	ns			
Turn-On Rise Time	t _r	_	20	_	ns	$V_{DS} = -10V, V_{GS} = -4.5V,$		
Turn-Off Delay Time	t _{D(off)}	_	38	_	ns	$R_L = 10\Omega$, $R_G = 6\Omega$		
Turn-Off Fall Time	t _f		41		ns			
Input Capacitance	C _{iss}	_	443	_	pF	10// // 0//		
Output Capacitance	Coss	_	125	_	pF	$V_{DS} = -16V, V_{GS} = 0V$ f = 1.0MHz		
Reverse Transfer Capacitance	C _{rss}	_	98	_	pF			

Notes:

- 5. Test pulse width $t=300\mu s$. 6. Guaranteed by design. Not subject to production testing.







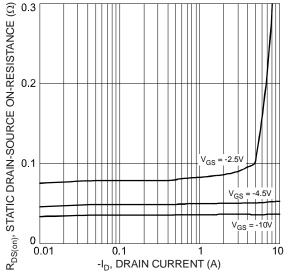


Fig. 3 On-Resistance vs. Drain Current and Gate Voltage

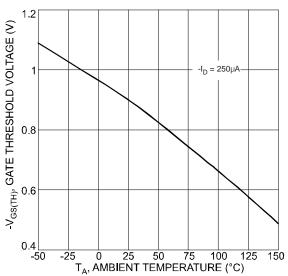


Fig. 5 Gate Threshold Voltage vs. Ambient Temperature

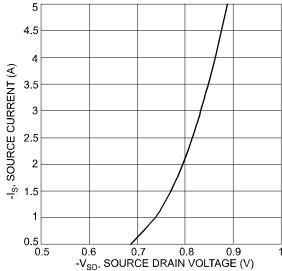
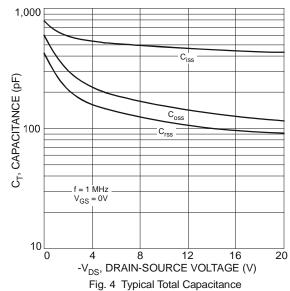


Fig. 7 Reverse Drain Current vs. Source-Drain Voltage



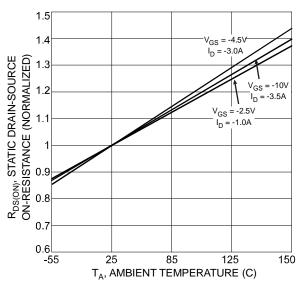


Fig. 6 Normalized Static Drain-Source On-Resistance vs. Ambient Temperature

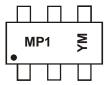


Ordering Information (Note 7)

Part Number	Case	Packaging
DMP2130LDM-7	SOT-26	3000/Tape & Reel

Notes: 7. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information

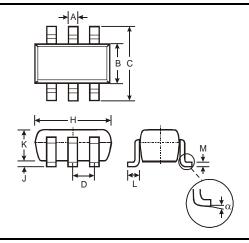


MP1 = Product Type Marking Code YM = Date Code Marking Y = Year ex: U = 2007 M = Month ex: 9 = September

Date Code Key

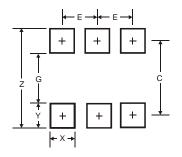
Year	20	07	20	08	20	09	20	10	20	11	20	12
Code	Į	J	\	/	V	٧)	<	`	Y	Z	7
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

Package Outline Dimensions



SOT-26							
Dim	Min	Max	Тур				
Α	0.35	0.50	0.38				
В	1.50	1.70	1.60				
С	2.70	3.00	2.80				
D	_		0.95				
Н	2.90	3.10	3.00				
J	0.013	0.10	0.05				
K	1.00	1.30	1.10				
L	0.35	0.55	0.40				
M	0.10	0.20	0.15				
α	0°	8°	_				
All Dimensions in mm							

Suggested Pad Layout



Dimensions	Value (in mm)
Z	3.20
G	1.60
Х	0.55
Y	0.80
С	2.40
Е	0.95

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